

# HL6501MG

## Visible High Power Laser Diode

ODE2031-00 (M)

Rev.0

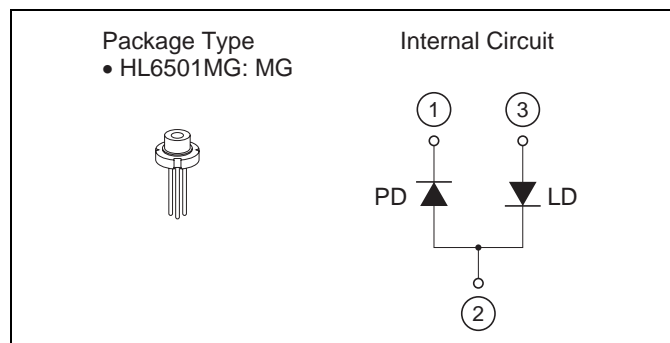
Aug. 01, 2008

### Description

The HL6501MG is a 0.65  $\mu\text{m}$  band AlGaInP laser diode (LD) with a multi-quantum well (MQW) structure. It is suitable as a light source for large capacity optical disc memories and various other types of optical equipment. Hermetic sealing of the small package ( $\phi 5.6$  mm) assures high reliability.

### Features

- High output power: 35 mW (CW)
- Visible light output:  $\lambda_p = 658$  nm Typ
- Small package:  $\phi 5.6$  mm
- Low astigmatism: 6  $\mu\text{m}$  Typ ( $P_O = 5$  mW)
- Single longitudinal mode



### Absolute Maximum Ratings

( $T_C = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Optical output power	$P_O$	35	mW
Pulse optical output power	$P_{O(\text{pulse})}$	50 *	mW
LD reverse voltage	$V_{R(\text{LD})}$	2	V
PD reverse voltage	$V_{R(\text{PD})}$	30	V
Operating temperature	$T_{opr}$	-10 to +60	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40 to +85	$^\circ\text{C}$

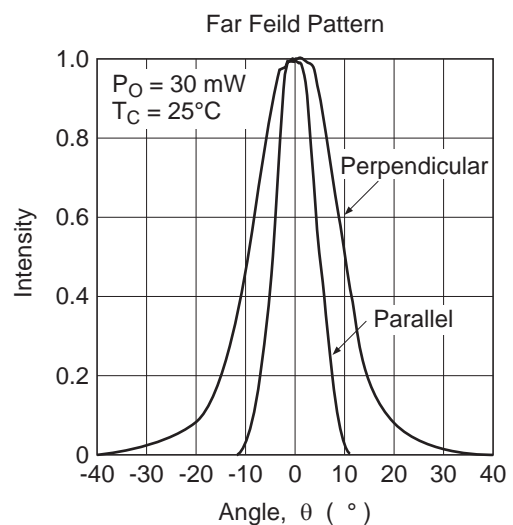
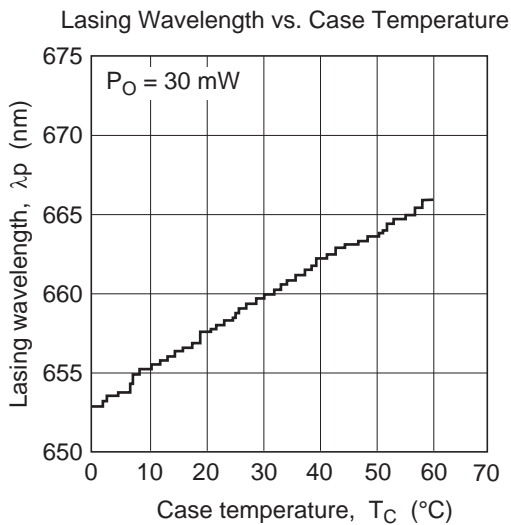
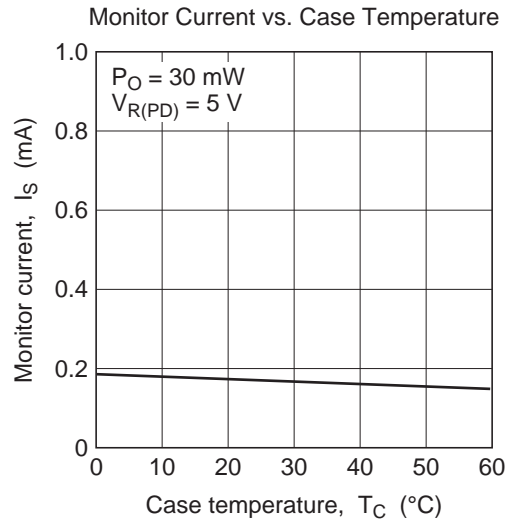
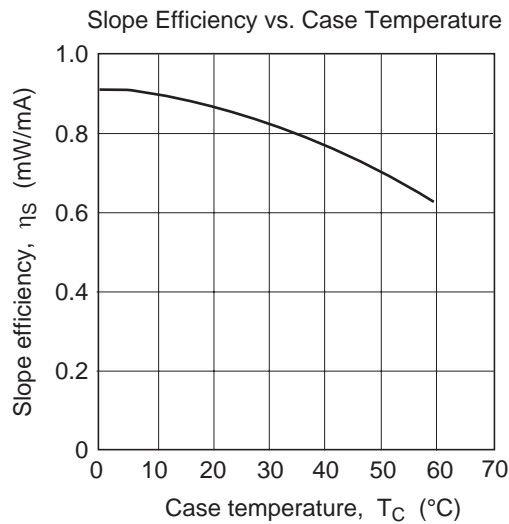
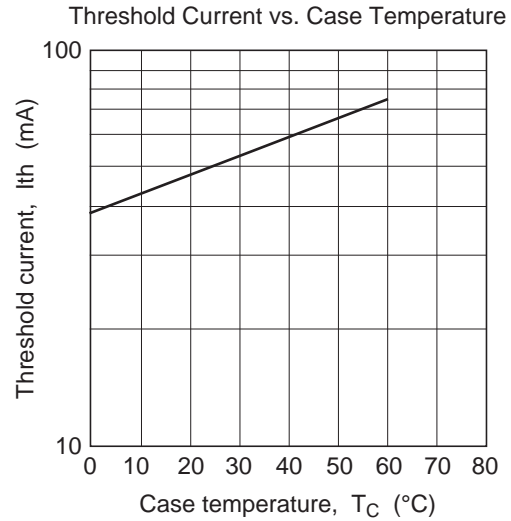
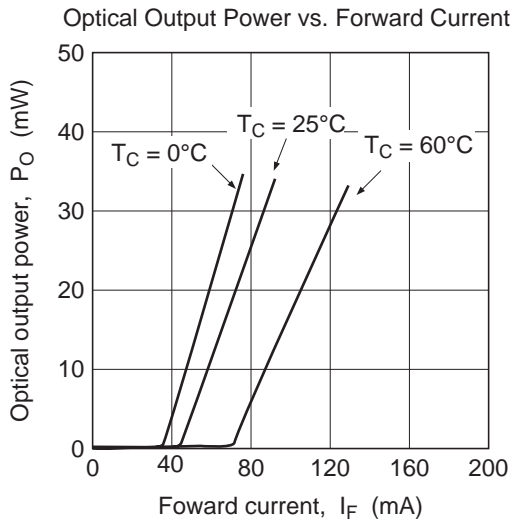
Note: Pulse condition : Pulse width = 100 ns , duty = 50%

### Optical and Electrical Characteristics

( $T_C = 25^\circ\text{C}$ )

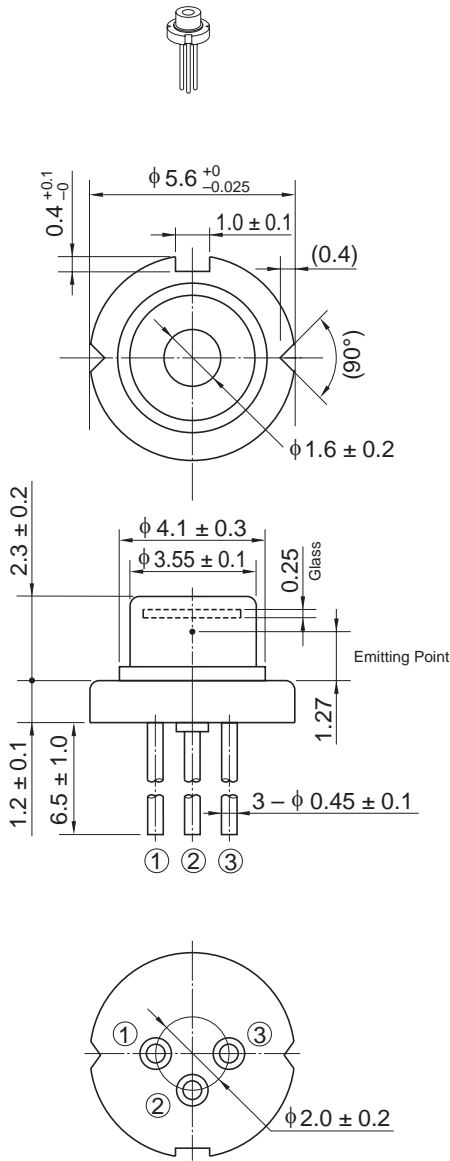
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Threshold current	$I_{th}$	30	45	70	mA	—
Operating voltage	$V_{OP}$	2.1	2.6	3.0	V	$P_O = 30$ mW
Slope efficiency	$\eta_s$	0.5	0.75	1.0	mW/mA	$18$ (mW) / ( $I_{(24\text{mW})} - I_{(6\text{mW})}$ )
Beam divergence parallel to the junction	$\theta_{//}$	7	8.5	10.5	$^\circ$	$P_O = 30$ mW
Beam divergence perpendicular to the junction	$\theta_{\perp}$	18	22	26	$^\circ$	$P_O = 30$ mW
Astigmatism	$A_s$	—	6	—	$\mu\text{m}$	$P_O = 5$ mW, NA = 0.55
Lasing wavelength	$\lambda_p$	645	658	665	nm	$P_O = 30$ mW
Monitor current	$I_s$	0.05	0.2	1.5	mA	$P_O = 30$ mW, $V_{R(\text{PD})} = 5$ V

### Typical Characteristic Curves



Package Dimensions

As of July, 2002  
Unit: mm



OPJ Code	LD/MG
JEDEC	—
JEITA	—
Mass (reference value)	0.3 g

## Cautions

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3. Definition of items shown in this CAS is in accordance with that shown in Opto Device Databook issued by OPJ unless otherwise specified.

## Sales Offices



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